

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of:	Peter Pegler	Confirmation No.:	9290
Patent No.:	6,812,079	Issue Date:	November 2, 2004
Serial No.:	10/677,570	Filing Date:	October 1, 2003
For:	Method for a Junction Field Effect Transistor with Reduced Gate Capacity	Attorney Docket No.:	65860-5028-US (formerly LOVO-041.DIV)

**TRANSMITTAL OF POWER OF ATTORNEY BY ASSIGNEE
REVOKING PREVIOUS POWERS OF RECORD**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450


Sir:

Applicant's attorney encloses herewith a Revocation and Power of Attorney by Assignee and Statement Under 37 CFR 3.73(b) for the above identified application.

Please change the attorney docket number to 65860-5028-US. Future correspondence should be forwarded to customer no. **24341**.

The Commissioner is authorized to charge any fees associated with this communication to Morgan, Lewis & Bockius LLP deposit account no. 50-0310 (order no. 65860-5028-US). A copy of this sheet is enclosed for such purpose.

Date: November 17, 2006



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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: See Schedule A
Serial No.: See Schedule A
Filed: See Schedule A
For: See Schedule A Attorney Docket No: See Schedule A

REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

S I R:

Lovoltech Inc., owner of the entire right, title and interest in, to and under the invention listed above hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, **Customer No. 24341**, and each of them, its attorneys, to prosecute this application, and to transact all business in the Patent and Trademark Office connected therewith, said appointment to be to the exclusion of the inventors and their attorney(s) in accordance with the provisions of 37 C.F.R. 3.71, provided that, if any one of these attorneys ceases being affiliated with the law firm of Morgan, Lewis & Bockius LLP as partner, counsel, or employee, then the appointment of that attorney and all powers derived therefrom shall terminate on the date such attorney ceases being so affiliated.

Please direct all future correspondence to the address associated with **Customer No. 24341**, Morgan, Lewis & Bockius LLP and direct all telephone calls to Morgan, Lewis & Bockius LLP at (650) 843-4000.

Assignee:	Lovoltech Inc.
Date:	<u>October 30, 2006</u>
Signature:	<u>Richard Francis</u>
Typed Name:	<u>RICHARD FRANCIS</u>
Position/Title:	<u>CHIEF TECHNICAL OFFICER</u>
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SCHEDULE A

Serial No./ Patent No:	Filing Date/Issue Date:	Title	Inventor(s)	Attorney Docket No.
09/430,500 6,251,716	10/29/1999 06/26/2001	Novel JFET Structure and Manufacturing Method for Low On-Resistance and Low Voltage	Ho-Yuan Yu	65860-5007-US
09/690,703 6,486,011	10/16/2000 11/26/2002	Novel JFET Structure and Manufacturing Method for Low On-Resistance and Low Voltage	Ho-Yuan Yu	65860-5008-US
09/458,571 6,307,223	12/09/1999 10/23/2001	Complimentary Junction Field Effect Transistors	Ho-Yuan Yu	65860-5009-US
09/453,136 6,674,107	12/02/1999 01/06/2004	Enhancement Mode Junction Field Effect Transistor with Low on Resistance	Ho-Yuan Yu	65860-5010-US
09/690,690 6,621,722	10/16/2000 09/16/2003	Rectifier Circuits with Low Forward Voltage JFET Device	Ho-Yuan Yu	65860-5011-US
09/453,165 6,304,007	12/02/1999 10/16/2001	Switcher for Switching Capacitors	Ho-Yuan Yu	65860-5013-US
09/453,141 6,281,705	12/02/1999 08/28/2001	Power Supply Module in Integrated Circuits	Ho-Yuan Yu	65860-5014-US
09/835,616 6,542,001	04/10/2001 04/01/2003	Power Supply Module in Integrated Circuits	Ho-Yuan Yu	65860-5015-US
09/741,488 6,349,047	12/18/2000 02/19/2002	Full Wave Rectifier Circuit Using Normally Off JFETS	Ho-Yuan Yu	65860-5016-US
09/915,987 6,549,439	07/25/2001 04/15/2003	Full Wave Rectifier Circuit Using Normally Off JFETS	Ho-Yuan Yu	65860-5017-US
09/669,480 6,355,513	09/25/2000 03/12/2002	Asymmetric Depletion Region for Normally Off JFET	Ho-Yuan Yu	65860-5018-US
10/360,450 6,734,715	02/05/2003 05/11/2004	Two Terminal Rectifier Using Normally Off JFET	Ho-Yuan Yu	65860-5019-US
09/670,176 6,566,936	09/25/2000 05/20/2003	Two Terminal Rectifier Using Normally Off JFET	Ho-Yuan Yu	65860-5020-US
09/708,336	11/07/2000	Starter Device for Normally Off JFETS	Ho-Yuan Yu	65860-5021-US

Serial No./ Patent No:	Filing Date/Issue Date:	Title	Inventor(s)	Attorney Docket No.
6,614,289	09/02/2003			
10/609,253 6,957,157	06/26/2003 12/13/2005	Starter Device for Normally Off JFETS	Ho-Yuan Yu	65860-5022-US
09/785,972 6,356,059	02/16/2001 03/12/2002	Buck Converter with Normally Off JFET	Ho-Yuan Yu	65860-5023-US
09/877,351 6,580,252	06/07/2001 06/17/2003	Boost Circuit with Normally Off JFET	Ho-Yuan Yu	65860-5024-US
10/371,856 7,098,634	02/21/2003 08/29/2006	Buck-Boost Circuit with Normally Off JFET	Ho-Yuan Yu	65860-5025-US
09/676,370 6,750,698	09/29/2000 06/15/2004	Cascade Circuits Utilizing Normally-Off Junction Field Effect Transistors for Low On-Resistance and Low Voltage Applications	Ho-Yuan Yu	65860-5026-US
10/278,303 6,696,706	10/22/2002 02/24/2004	Structure for a Junction Field Effect Transistor with Reduced Gate Capacitance	Peter Pegler	65860-5027-US
10/677,570 6,812,079	10/01/2003 11/02/2004	Method for a Junction Field Effect Transistor with Reduced Gate Capacity	Peter Pegler	65860-5028-US
09/892,128 6,528,880	10/01/2003 11/02/2004	Semiconductor Package for Power JFET Having Copper Plate for Source and Ribbon Contact for Gate	Bill Planey	65860-5029-US
10/215,570 6,747,342	08/09/2002 06/08/2004	Flip-Chip Packaging	William Planey	65860-5030-US
10/158,326	05/29/2002	Method and Structure for Reduced Gate Capacitance in a JFET	Ho-Yuan Yu et al.	65860-5031-US
10/191,030 6,777,722	07/02/2002 08/17/2004	Method and Structure for Double Dose Gate in a JFET	Ho-Yuan Yu	65860-5032-US
10/867,972 6,995,052	06/14/2004 02/07/2006	Method and Structure for Double Dose Gate in a JFET	Ho-Yuan Yu et al.	65860-5033-US
10/153,012 6,921,932	05/20/2002 07/26/2005	JFET and MESFET Structures for Low Voltage, High Current and High Frequency Applications	Ho-Yuan Yu	65860-5034-US
11/121,381	05/03/2005	JFET and MESFET Structures for Low	Ho-Yuan Yu	65860-5035-US

Serial No./ Patent No:	Filing Date/Issue Date:	Title	Inventor(s)	Attorney Docket No.
7,045,397	05/16/2006	Voltage, High Current and High Frequency Applications		
11/406,469	04/17/2006	JFET and MESFET Structures for Low Voltage, High Current and High Frequency Applications	Ho-Yuan Yu	65860-5036-US
10/117,019 6,900,506	04/04/2002 05/31/2005	Method and Structure for a High Voltage Junction Field Effect Transistor	Ho-Yuan Yu	65860-5037-US
10/439,558 6,887,768	05/15/2003 05/03/2005	Method and Structure for Composite Trench Fill	Ho-Yuan Yu	65860-5038-US
10/379,768 7,009,228	03/04/2003 03/07/2006	Guard Ring Structure and Method for Fabricating Same	Ho-Yuan Yu	65860-5039-US
10/382,344 7,038,260	03/04/2003 05/02/2006	Dual Gate Structure for a FET and Method for Fabricating Same	Ho-Yuan Yu	65860-5040-US
10/209,211 6,661,276	07/29/2002 12/09/2003	MOSFET Driver Matching Circuit for an Enhancement Mode JFET	Daniel Chang	65860-5041-US
10/355,403 7,075,132	12/30/2002 07/11/2006	Programmable Junction Field Effect Transistor and Method for Programming Same	Ho-Yuan Yu	65860-5044-US
11/086,199	03/21/2005	Programmable Junction Field Effect Transistor and Method for Programming Same	Ho-Yuan Yu et al.	65860-5045-US
10/683,719	10/09/2003	Structure and Method for Enhanced Performance in Semiconductor Substrates	Chong-Ming Lin et al.	65860-5046-US
10/279,806 6,774,417	10/23/2002 08/20/2004	Electrostatic Discharge Protection Device for Integrated Circuits	Chong-Ming Lin et al.	65860-5047-US
10/793,077 7,009,229	03/03/2004 03/07/2006	Electrostatic Discharge Protection Device for Integrated Circuits	Chong-Ming Lin et al.	65860-5048-US
11/110,507	04/19/2005	Multiple Doped Channel in a Multiple Doped Gate Junction Field Effect Transistor	Ho-Yuan Yu et al.	65860-5051-US
11/149,716	06/10/2005	Field Effect Transistor and Method of Manufacturing the Same	Jian Li et al.	65860-5052-US
11/378,412	03/16/2006	Composite Field Effect Transistor	Jonathan Klein et al.	65860-5057-US

Serial No:/ Patent No:	Filing Date/Issue Date:	Title	Inventor(s)	Attorney Docket No.
11/320,313	12/27/2005	Ultrasoft Recovery Diode	Richard Francis et al.	65860-5058-US